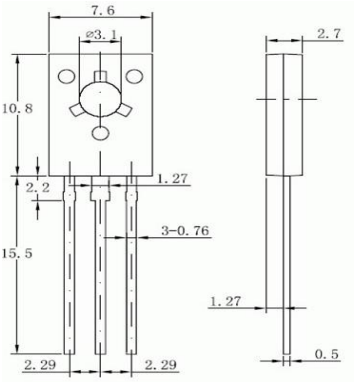
OTOMO

Otomo Semiconductor (Shenzhen) Co., LTD

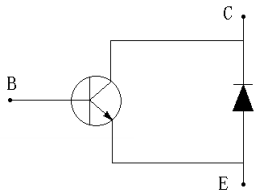
Model：13003F **Appearance：TO-126** **Product name: Silicon material amplifier transistor**

TO-126 outline diagram

Polarity: Three pins from left to right 1: B (base) 2: C (collector) 3: E (emitter)



Uses: Mainly used in energy-saving lamps, rectifiers, special switching circuit



Limit range (TA=25 ° C unless otherwise specified)

Project	Symbol	Rated value	Unit
Collector-emitter voltage（IB=0）	VCEO	400	V
Collector-base voltage	VCBO	700	V
Emitter-base voltage	VEBO	9	V
Collector current	IC	1.5	A
Collector dissipation power	PC	2	W
Junction temperature	Tjm	150	℃
Storage temperature	Tstg	-55~+150	℃

Electrical parameter characteristics (T_A=25℃ unless otherwise specified)

Project	Symbol	Test condition	Min value	Max value	Unit
Collector-base cutoff current	ICBO	VCB=630V,IE=0		1	uA
Emitter-base cut-off current	IEBO	VEB=9V,IC=0		1	uA
Collector-emitter voltage	BVCEO	IC=1mA	410	520	V
Collector-emitter voltage	BVCBO	IC=0.1mA	700		V
Collector-emitter voltage	BVEB	IE=0.1mA	9		V
Collector-emitter saturation voltage	VCESat	Ic=1A,IB=200mA		0.5	V
Base-emitter saturation voltage	VBESat	Ic=1A,IB=200mA		1	V
Current amplification	HFE	VCE=5V,IC=0.2A	15	30	
Storage time	Ts	IC=0.25A	2	3.5	uS